2SB776

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

$V_{CE(sat)}$,h_{FE}

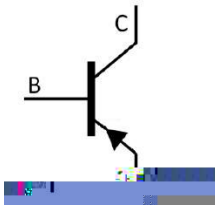
Low saturation voltage, excellent h_{FE} linearity and high h_{FE}.

/ Applications

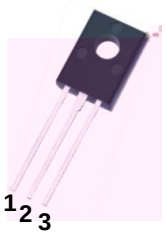
,

Power amplifier and switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

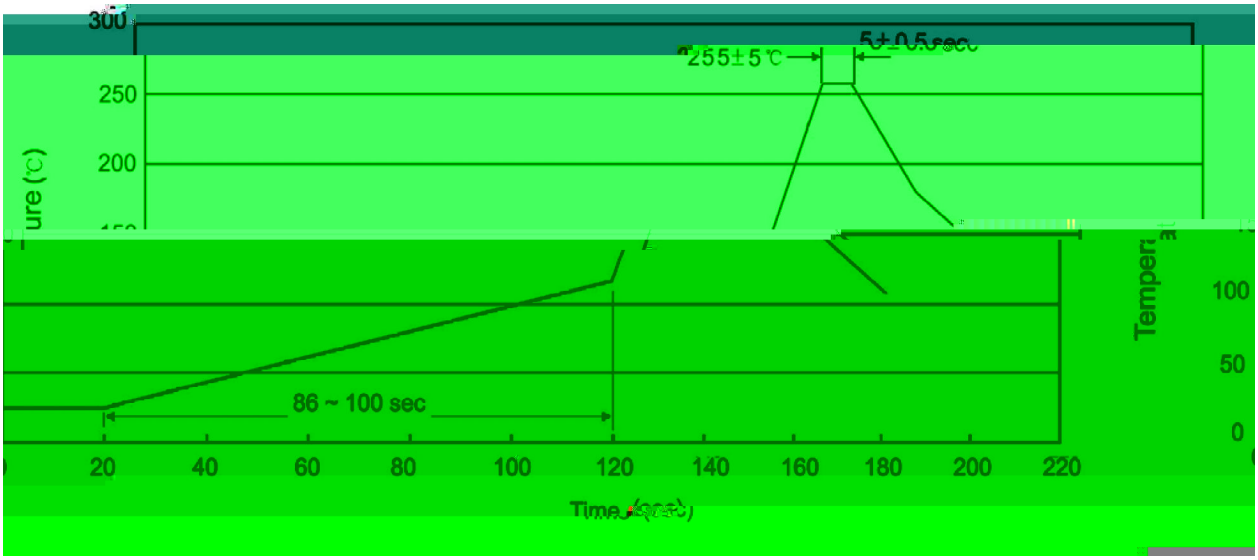
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Peak Collector Current – Continuous	I_{CM}	-7.0	A
Base Current - Continuous	I_B	-0.6	A
Collector Power Dissipation	P_C (Tc=25)	10	W
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA I_E=0	-50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-5mA I_B=0	-50			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-100μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-50V I_E=0			-1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-3.0V I_C=0			-1.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-1.0A	100		400	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-20mA	100			
Collector to Emitter Saturation Voltage	V					

( ) / Temperature Profile for Dip Soldering(Pb-Free)



				Note:	
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm^3)

/ TUBE

Package Type	Units	Dimension	(unit mm^3)